

WHAT IS CLAIMED IS:

1. A method of manufacturing circuit devices, comprising:

preparing a laminated plate by laminating a first conductive film and a second conductive film via a third conductive film;

forming a conductive pattern layer by etching said first conductive film into a desirable pattern;

removing the third conductive film by use of said conductive pattern layer as a mask and thus forming anchor portions where said third conductive film is depressed further inside than said conductive pattern layer;

fixedly fitting semiconductor elements on said conductive pattern layer;

electrically connecting electrodes of said semiconductor elements with predetermined parts of said conductive pattern layer;

covering said semiconductor elements with a sealing resin layer and filling said sealing resin layer into said anchor portions; and

exposing said sealing resin layer and said third conductive film on the rear surface by removing said second conductive film.

2. The method of Claim 1, wherein said third conductive film is used as an etching stopper when the first conductive film is etched.

3. The method of Claim 2, wherein a solution containing ferric chloride or cupric chloride is used as a solution to perform said etching.

4. The method of Claim 1, wherein said anchor portions are formed by overetching said third conductive film by use of said conductive pattern layer as a mask.

5. The method of Claim 4, wherein said etching solution is an iodine-based solution.

6. The method of Claim 1, wherein said third conductive film is peeled off by electrolysis by use of said conductive pattern layer as a mask, and said anchor portions are formed by over-peeling.

7. The method of Claim 1, wherein said third conductive film and said sealing resin layer in said anchor portions remaining after entirely etching the second conductive film are exposed.

8. The method of Claim 7, wherein external electrodes are formed by adhering a brazing filler material to the remaining third conductive film.

9. A method of manufacturing circuit devices, comprising:

preparing a laminated plate by laminating a first conductive film and a second conductive film via a third conductive film;

selectively forming pads of a fourth conductive film on said first conductive film;

forming a conductive pattern layer by etching said first conductive film into a desirable pattern;

removing said third conductive film by use of the conductive pattern layer as a mask and thus forming anchor portions where said third conductive film is depressed further inside than said conductive pattern layer;

fixedly fitting semiconductor elements on said conductive pattern layer;

electrically connecting electrodes of said semiconductor elements with said pads on predetermined parts of said conductive pattern layer;

covering said semiconductor elements with a sealing resin layer and filling said sealing resin layer into said anchor portions; and

exposing said sealing resin layer and said third conductive film on the rear surface by removing said second conductive film.

10. The method of Claim 9, wherein said third conductive film is used as an etching stopper when the first conductive film is etched.

11. The method of Claim 10, wherein a solution containing ferric chloride or cupric chloride is used as a solution to perform said etching.

12. The method of Claim 9, wherein said anchor portions are formed by overetching said third conductive film by use of said conductive pattern layer as a mask.

13. The method of Claim 12, wherein said etching solution is an iodine-based solution.

14. The method of Claim 9, wherein said third conductive film is peeled off by electrolysis by use of said conductive pattern layer as a mask, and said anchor portions are formed by over-peeling.

15. The method of Claim 9, wherein said third conductive film and said sealing resin layer in said anchor portions remaining after entirely etching the second conductive film are exposed.

16. The method of Claim 15, wherein external electrodes are formed by adhering a brazing filler material to the remaining third conductive film.